

FQP12N60C

Power MOSFET, N-Channel, QFET[®], 600 V, 12 A, 650 mΩ, TO-220

Product Overview

For complete documentation, see the data sheet.

These N-Channel enhancement mode power field effect transistors are produced using ON Semiconductor's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies, active power factor correction, electronic lamp ballast based on half bridge topology.

Features

- 12 A, 600 V, $R_{DS(on)} = 650 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 6 \text{ A}$
- Low Gate Charge (Typ. 48 nC)
- Low C_{rss} (Typ. 21 pF)
- 100% Avalanche Tested